

Silicon Carbide Schottky Diode

IDW30G120C5B

5th Generation thinQ!TM 1200 V SiC Schottky Diode

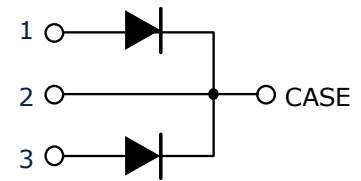
Final Datasheet

Rev. 2.0 2014-06-10

thinQ!™ SiC Schottky Diode

Features:

- Revolutionary semiconductor material - Silicon Carbide
- No reverse recovery current / No forward recovery
- Temperature independent switching behavior
- Low forward voltage even at high operating temperature
- Tight forward voltage distribution
- Excellent thermal performance
- Extended surge current capability
- Specified dv/dt ruggedness
- Qualified according to JEDEC¹⁾ for target applications
- Pb-free lead plating; RoHS compliant



Benefits

- System efficiency improvement over Si diodes
- Enabling higher frequency / increased power density solutions
- System size/cost savings due to reduced heatsink requirements and smaller magnetics
- Reduced EMI
- Highest efficiency across the entire load range
- Robust diode operation during surge events
- High reliability
- RelatedLinks: www.infineon.com/sic



Applications

- Solar inverters
- Uninterruptable power supplies
- Motor drives
- Power Factor Correction



Package pin definitions

- Pin 1 – anode 1
- Pin 2 and backside – cathode
- Pin 3 – anode 2



Key Performance and Package Parameters (leg/device)

Type	V _{DC}	I _F	Q _C	T _{j,max}	Marking	Package
IDW30G120C5B	1200 V	15 / 30 A	77 / 154 nC	175°C	D3012B5	PG-TO247-3

1) J-STD20 and JESD22

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Maximum ratings

Parameter	Symbol	Value (leg/device)	Unit
Repetitive peak reverse voltage	V_{RRM}	1200	V
Continuous forward current for $R_{th(j-c,max)}$ $T_C = 150^\circ\text{C}$, $D=1$ $T_C = 135^\circ\text{C}$, $D=1$ $T_C = 25^\circ\text{C}$, $D=1$	I_F	15 / 30 20 / 40 44 / 87	A
Surge non-repetitive forward current, sine halfwave $T_C=25^\circ\text{C}$, $t_p=10\text{ms}$ $T_C=150^\circ\text{C}$, $t_p=10\text{ms}$	$I_{F,SM}$	120 / 240 115 / 230	A
Non-repetitive peak forward current $T_C = 25^\circ\text{C}$, $t_p=10 \mu\text{s}$	$I_{F,max}$	1230 / 2460	A
i^2t value $T_C = 25^\circ\text{C}$, $t_p=10 \text{ms}$ $T_C = 150^\circ\text{C}$, $t_p=10 \text{ms}$	$\int i^2 dt$	72 / 288 66 / 264	A ² s
Diode dv/dt ruggedness $V_R=0\dots960 \text{V}$	dv/dt	80	V/ns
Power dissipation for $R_{th(j-c,max)}$ $T_C = 25^\circ\text{C}$	P_{tot}	166 / 332	W
Operating and storage temperature	$T_j; T_{stg}$	-55...175	°C
Soldering temperature, wavesoldering only allowed at leads 1.6mm (0.063 in.) from case for 10 s	T_{sold}	260	°C
Mounting torque M3 and M4 screws	M	0.7	Nm

Thermal Resistances

Parameter	Symbol	Conditions	Value (leg/device)			Unit
			min.	typ.	max.	
Characteristic						
Diode thermal resistance, junction – case	$R_{th(j-c)}$		-	0.7/0.35	0.9/0.5	K/W
Thermal resistance, junction – ambient	$R_{th(j-a)}$	leaded	-	-	62	K/W

Electrical Characteristics
Static Characteristic, at T_j=25°C, unless otherwise specified

Parameter	Symbol	Conditions	Value (leg/device)			Unit
			min.	typ.	max.	
DC blocking voltage	V _{DC}	T _j = 25°C	1200	-	-	V
Diode forward voltage	V _F	I _F = 15/30 A, T _j =25°C	-	1.4	1.65	V
		I _F = 15/30 A, T _j =150°C	-	1.7	2.30	
Reverse current	I _R	V _R =1200 V, T _j =25°C		9 / 17	124 / 248	μA
		V _R =1200 V, T _j =150°C		44 / 88	640 / 1280	

Dynamic Characteristics, at T_j=25°C, unless otherwise specified

Parameter	Symbol	Conditions	Value (leg/device)			Unit
			min.	typ.	max.	
Total capacitive charge	Q _C	V _R = 800V, T _j =150° C & 25°C $Q_C = \int_0^{V_R} C(V)dV$	-	77 / 154	-	nC
Total Capacitance	C	V _R =1 V, f=1 MHz	-	990 / 1980	-	pF
		V _R =400 V, f=1 MHz	-	70 / 140	-	
		V _R =800 V, f=1 MHz	-	55 / 111	-	

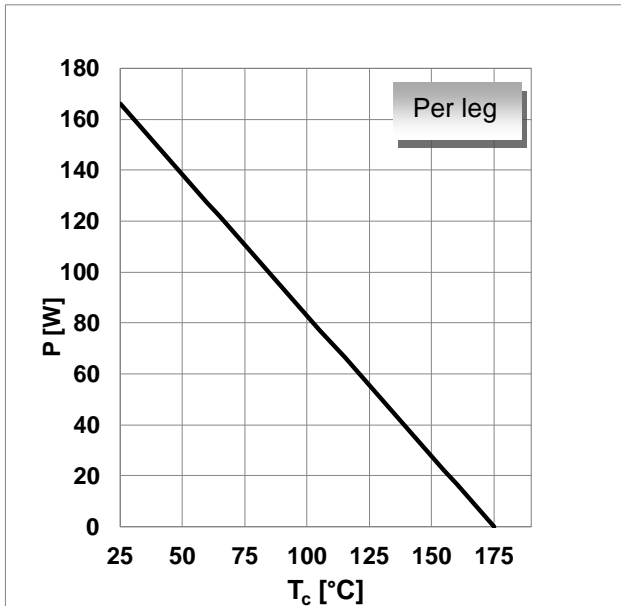


Figure 1. Power dissipation per leg as function of case temperature, $P_{tot}=f(T_C)$, $R_{th(j-c),max}$

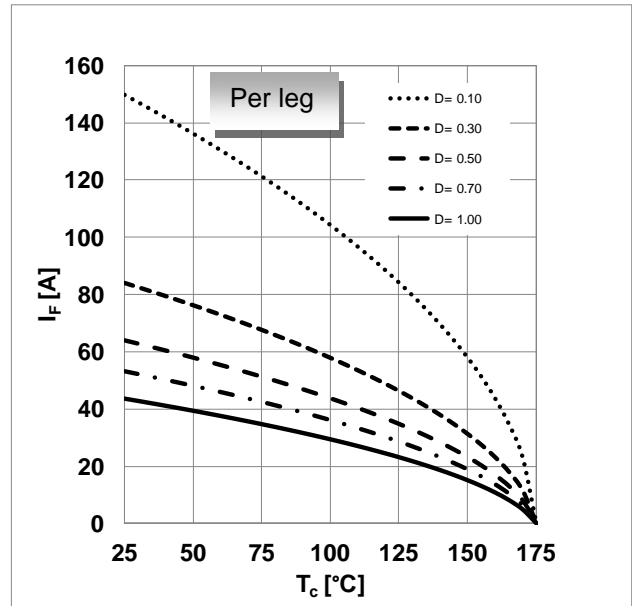


Figure 2. Diode forward current per leg as function of temperature, parameter: $T_j \leq 175^\circ\text{C}$, $R_{th(j-c),max}$, D =duty cycle, V_{th} , R_{diff} @ $T_j=175^\circ\text{C}$

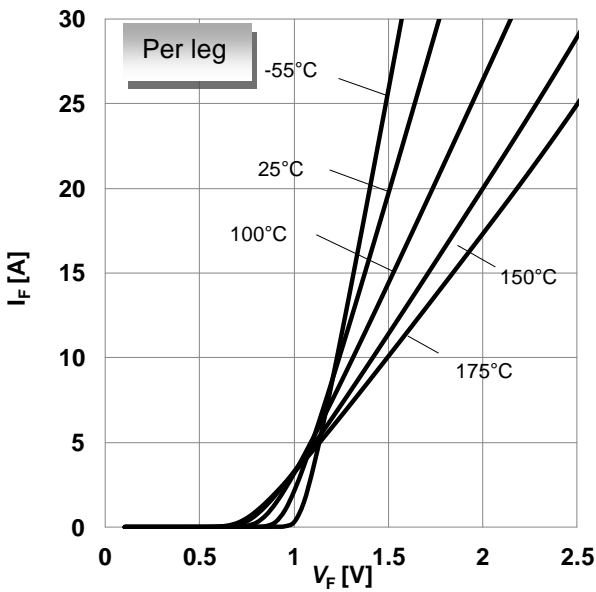


Figure 3. Typical forward characteristics per leg, $I_F=f(V_F)$, $t_p=10\ \mu\text{s}$, parameter: T_j

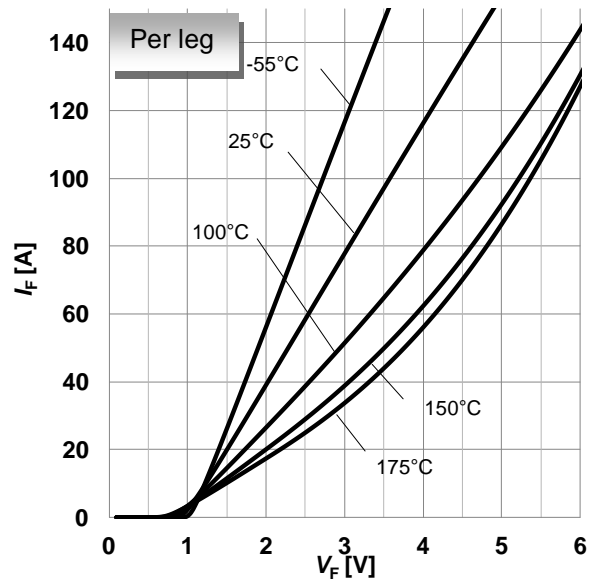


Figure 4. Typical forward characteristics in surge current per leg, $I_F=f(V_F)$, $t_p=10\ \mu\text{s}$, parameter: T_j

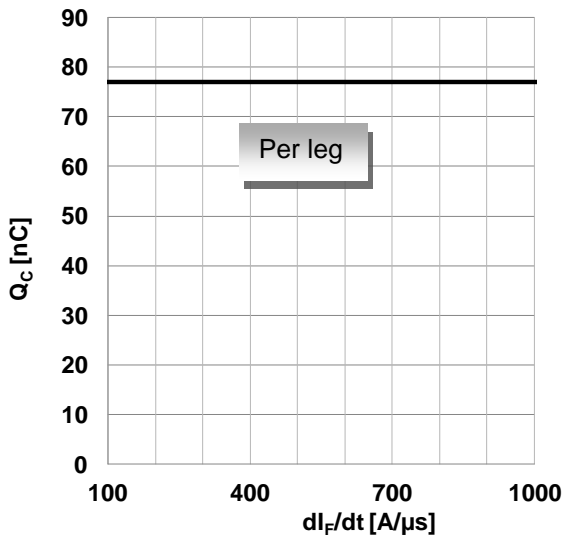


Figure 5. Typical capacitive charge per leg as function of current slope¹, $Q_C=f(di_F/dt)$, $T_j=150^\circ\text{C}$
 1) guaranteed by design.

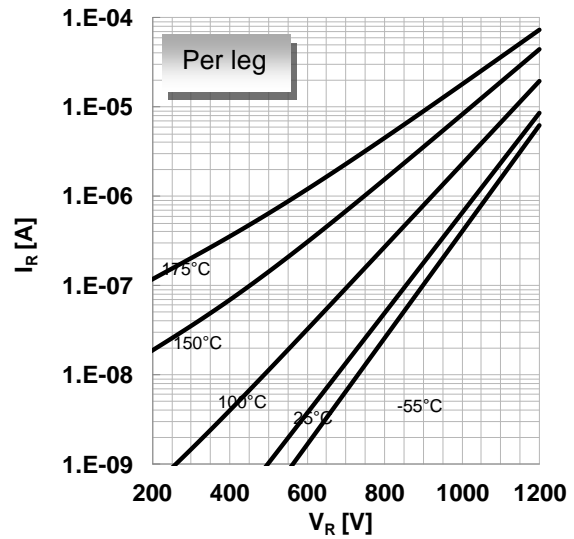


Figure 6. Typical reverse characteristics per leg, $I_R=f(V_R)$, parameter: T_j

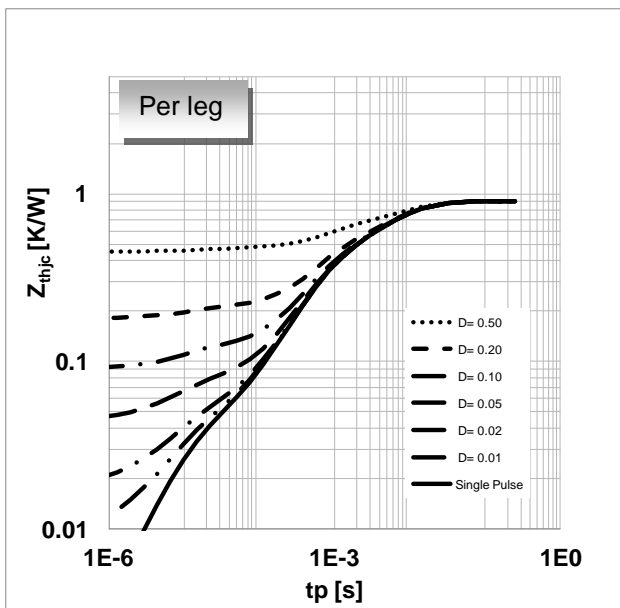


Figure 7. Max. transient thermal impedance per leg, $Z_{th,j-c}=f(t_p)$, parameter: $D=t_p/T$

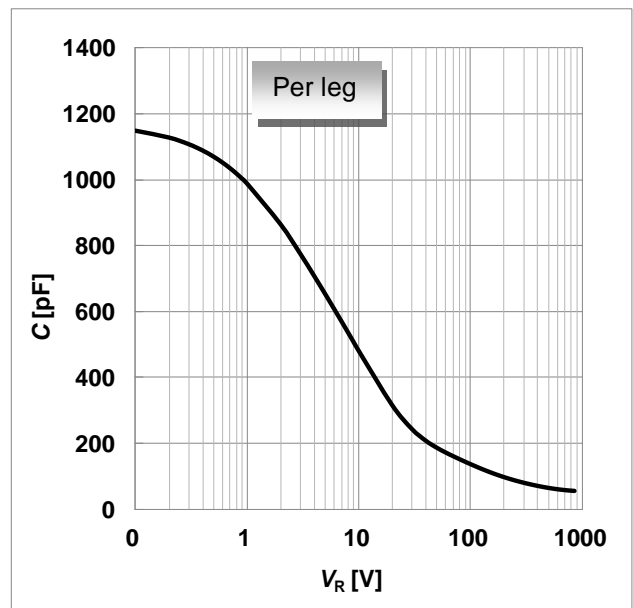


Figure 8. Typical capacitance per leg as function of reverse voltage, $C=f(V_R)$; $T_j=25^\circ\text{C}$; $f=1\text{ MHz}$

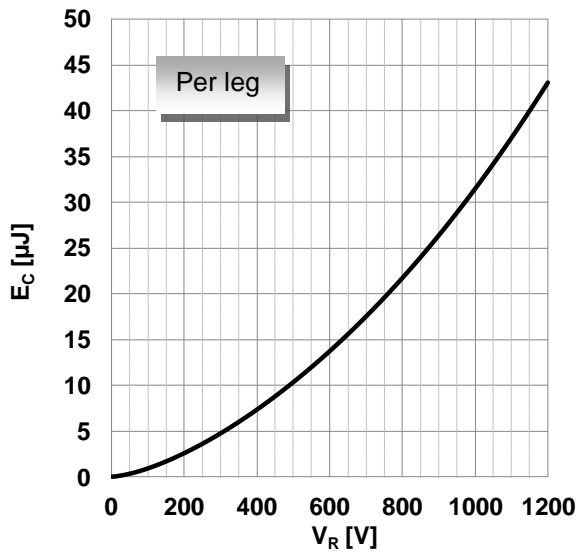
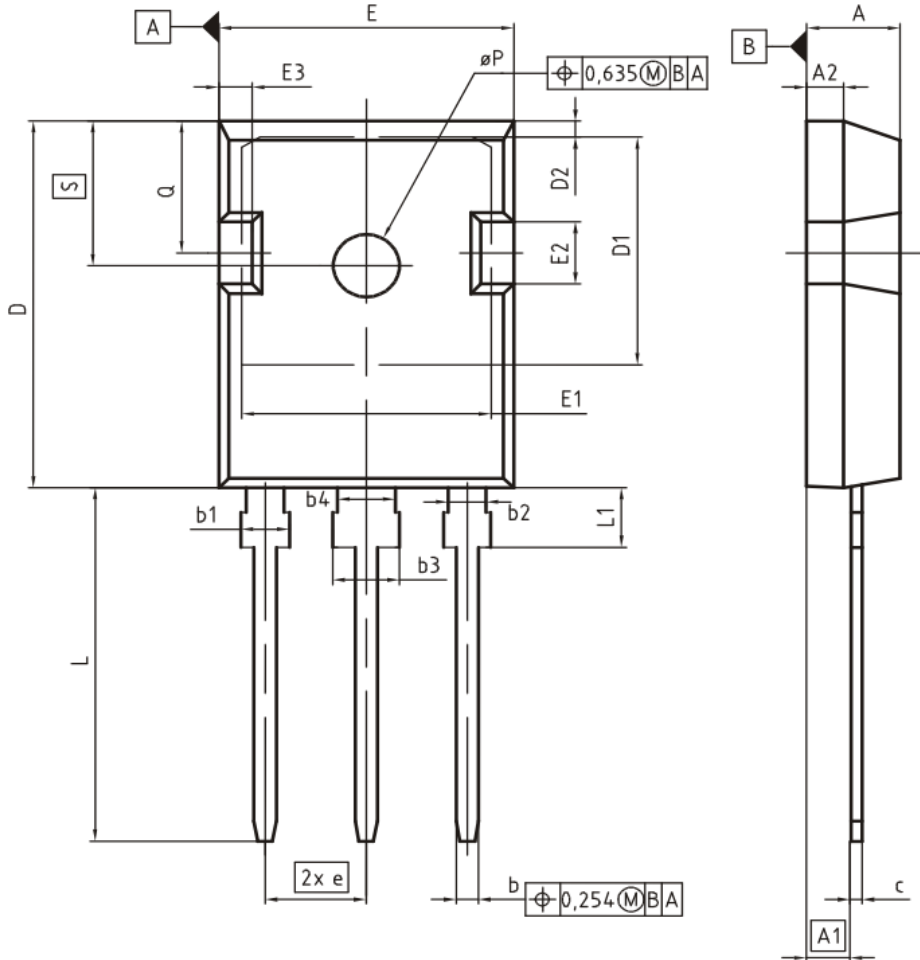


Figure 9. Typical capacitively stored energy as function of reverse voltage, per leg, $E_C=f(V_R)$

PG-TO247-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.83	5.21	0.190	0.205
A1	2.27	2.54	0.089	0.100
A2	1.85	2.16	0.073	0.085
b	1.07	1.33	0.042	0.052
b1	1.90	2.41	0.075	0.095
b2	1.90	2.16	0.075	0.085
b3	2.87	3.38	0.113	0.133
b4	2.87	3.13	0.113	0.123
c	0.55	0.68	0.022	0.027
D	20.80	21.10	0.819	0.831
D1	16.25	17.65	0.640	0.695
D2	0.95	1.35	0.037	0.053
E	15.70	16.13	0.618	0.635
E1	13.10	14.15	0.516	0.557
E2	3.68	5.10	0.145	0.201
E3	1.00	2.60	0.039	0.102
e	5.44 (BSC)		0.214 (BSC)	
N	3		3	
L	19.80	20.32	0.780	0.800
L1	4.10	4.47	0.161	0.176
ϕP	3.50	3.70	0.138	0.146
Q	5.49	6.00	0.216	0.236
S	6.04	6.30	0.238	0.248

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REVISION
05

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Previous Revision:

Revision	Date	Subjects (major changes since last version)
2.0	-	Final data sheet

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